TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

T C 7 M H 3 7 4 F K

Octal D-Type Flip-Flop with 3-State Output

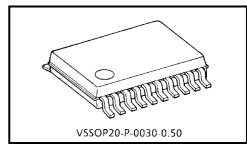
The TC7MH374FK is an advanced high speed CMOS octal flip-flop with 3-state output fabricated with silicon gate $\rm C^2MOS$ technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

This 8-bit D-type flip-flop is controlled by a clock input (CK) and an output enable input (\overline{OE}).

When the $\overline{\mbox{OE}}$ input is high, the eight outputs are in a high impedance state.

An input protection circuit ensures that 0 to 7 V can be applied



Weight: 0.03 g (typ.)

to the input pins without regard to the supply voltage. This device can be used to interface 5~V to 3~V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

- High speed: $f_{max} = 185 \text{ MHz}$ (typ.) (VCC = 5 V)
- Low power dissipation: $ICC = 4 \mu A \text{ (max) (Ta} = 25^{\circ}C)$
- High noise immunity: VNIH = VNIL = 28% VCC (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: tpLH = tpHL
- Wide operating voltage range: VCC (opr) = 2~5.5 V
- Low noise: VOLP = 0.8 V (max)
- Pin and function compatible with 74ALS374

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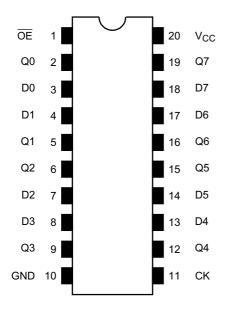
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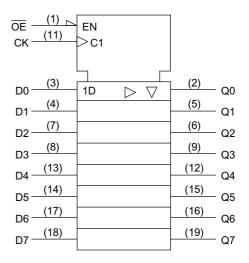
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Pin Assignment (top view)



IEC Logic Symbol



Truth Table

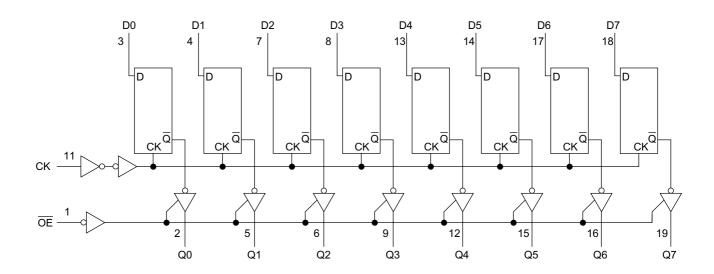
	Outputs		
ŌĒ	CK	D	Outputs
Н	Х	Х	Z
L	—	Х	Q _n
L		L	L
L		Н	Н

X: Don't care

Z: High impedance

Q_n: No change

System Diagram





Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	I _{CC}	±75	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0~5.5	V
Input voltage	V _{IN}	0~5.5	V
Output voltage	V _{OUT}	0~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	$0\sim100 \ (V_{CC}=3.3\pm0.3 \ V)$	ns/V
input rise and rail time	αί/αν	$0\sim20 \ (V_{CC}=5\pm0.5 \ V)$	115/ V



Electrical Characteristics

DC Characteristics

Characteristics		Symbol Test Condition		Condition		Ta = 25°C			Ta = -40~85°C		Unit
Charac	Rensucs	Symbol			V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic
					2.0	1.50	_	_	1.50	_	
Input voltage	High level	V_{IH}		_		V _{CC} × 0.7	_	_	V _{CC} × 0.7	_	V
input voitage					2.0	_	_	0.50	_	0.50	V
	Low level	V_{IL}		_	3.0~5.5	1	_	V _{CC} × 0.3	_	V _{CC} ×0.3	
					2.0	1.9	2.0		1.9		
		V _{ОН}		$I_{OH} = -50 \mu A$	3.0	2.9	3.0		2.9	_	
	High level		V _{IN} = V _{IH} or V _{IL}		4.5	4.4	4.5	_	4.4	_	
Output				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48		V
				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	_	
voltage					2.0	_	0	0.1	_	0.1	V
			., .,	$I_{OL} = 50 \mu A$	3.0	_	0	0.1	_	0.1	
	Low level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}		4.5	_	0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0	_	_	0.36	_	0.44	
	Ic		$I_{OL} = 8 \text{ mA}$	4.5	_	_	0.36	_	0.44		
3-state output	off-state current	I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		5.5	_	_	±0.25	_	±2.50	μА
Input leakage	current	I _{IN}	V _{IN} = 5.5 V or GND		0~5.5			±0.1	_	±1.0	μΑ
Quiescent sup	ply current	Icc	$V_{IN} = V_{CC}$	V _{IN} = V _{CC} or GND		_	_	4.0	_	40.0	μΑ



Timing Requirements (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		Ta = -40~85°C	Unit	
	Symbol	rest Condition	V _{CC} (V)	Тур.	Limit	Limit	Offic	
Minimum pulse width	t _{w (H)}		3.3 ± 0.3	_	5.0	5.5	ne	
(CK)	t _{w (L)}	_	5.0 ± 0.5		5.0	5.0	ns	
Minimum set-up time	t _s	_	3.3 ± 0.3	_	4.5	4.5	ns	
			5.0 ± 0.5		3.0	3.0	110	
Minimum hold time	t _h		3.3 ± 0.3	_	2.0	2.0	ns	
		_	5.0 ± 0.5	_	2.0	2.0	115	

AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol Test Condition				Ta = 25°C			Ta = -40~85°C		Unit
Characteristics	Symbol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Offic
			3.3 ± 0.3	15	_	8.1	12.7	1.0	15.0	
Propagation delay time	t _{pLH}		3.3 ± 0.3	50	_	10.6	16.2	1.0	18.5	ns
(CK-Q)	t _{pHL}	_	5.0 ± 0.5	15	_	5.4	8.1	1.0	9.5	115
			3.0 ± 0.5	50	_	6.9	10.1	1.0	11.5	
			3.3 ± 0.3	15	_	7.1	11.0	1.0	13.0	
3-state output enable time	t _{pZL}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	50	_	9.6	14.5	1.0	16.5	ns
3-state output enable time	t _{pZH}		5.0 ± 0.5	15	_	5.1	7.6	1.0	9.0	
			3.0 ± 0.5	50	_	6.6	9.6	1.0	11.0	
3-state output disable time	t _{pLZ}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	50	_	10.2	14.0	1.0	16.0	ns
3-state output disable time	t _{pHZ}		5.0 ± 0.5	50	_	6.1	8.8	1.0	10.0	
	f _{max}	_	3.3 ± 0.3	15	80	130	_	70	_	- MHz
Maximum clock frequency				50	55	85	_	50	_	
Maximum clock frequency			5.0 ± 0.5	15	130	185	_	110	_	
				50	85	120	_	75	_	
Output to output skew	t _{osLH}	(Note1)	3.3 ± 0.3	50	_	_	1.5	_	1.5	no
Output to output skew	t _{osHL}	(Note I)	5.0 ± 0.5	50	_	_	1.0	_	1.0	ns
Input capacitance	C _{IN}				_	4	10	_	10	pF
Output capacitance	C _{OUT}	-	_		_	6	_	_	_	pF
Power dissipation capacitance	C _{PD}			(Note2)	_	32	_	_	_	pF

Note1: This parameter is guaranteed by design.

 $t_{OSLH} = |t_{DLHm} - t_{DLHn}|, t_{OSHL} = |t_{DHLm} - t_{DHLn}|$

Note2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 (per F/F)$

And the total C_{PD} when n pcs of latch operate can be gained by the following equation:

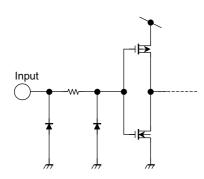
 C_{PD} (total) = 20 + 12• n



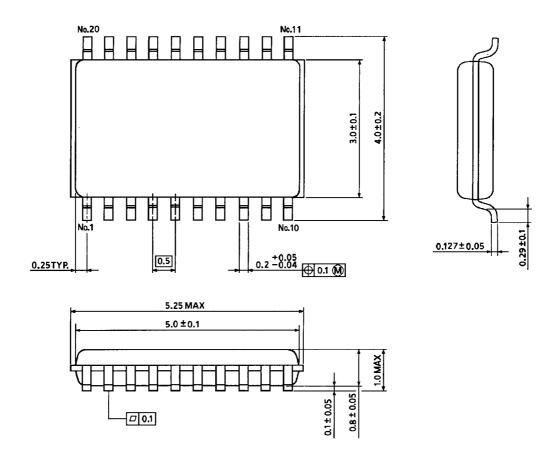
Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		Unit
Gilalacteristics	Syllibol	rest Condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	0.5	8.0	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-0.5	-0.8	V
Minimum high level dynamic input voltage V_{IH}	V _{IHD}	C _L = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage V_{IL}	V _{ILD}	C _L = 50 pF	5.0	_	1.5	V

Input Equivalent Circuit



Package Dimensions



Weight: 0.03 g (typ.)